

μ PA2460T1Q MOS FIELD EFFECT TRANSISTOR

Description

The μ PA2460T1Q is a switching device, which can be driven directly by a 2.5 V power source.

The μ PA2460T1Q features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

Features

- 2.5 V drive available
- Low on-state resistance
 - --- $R_{DS(on)1} = 17.5 \text{ m}\Omega \text{ MAX.} (V_{GS} = 4.5 \text{ V}, I_D = 3.0 \text{ A})$
 - ---- $R_{DS(on)2} = 18.5 \text{ m}\Omega \text{ MAX.} (V_{GS} = 4.0 \text{ V}, I_D = 3.0 \text{ A})$
 - --- $R_{DS(on)3} = 22.0 \text{ m}\Omega \text{ MAX.} (V_{GS} = 3.1 \text{ V}, I_D = 3.0 \text{ A})$
 - --- $R_{DS(on)4} = 27.5 \text{ m}\Omega \text{ MAX.} (V_{GS} = 2.5 \text{ V}, I_D = 3.0 \text{ A})$
- Built-in G-S protection diode against ESD

Ordering Information

Part No.	LEAD PLATING	PACKING	Package
μ PA2460T1Q-E1-AX ^{*1}	Ni/Pd/Au	8 mm embossed taping	8-pin HUSON (2720)
		3000 p/reel	

Note: *1. Pb-free (This product does not contain Pb in the external electrode and other parts.)

Absolute Maximum Ratings ($T_A = 25^{\circ}C$)

Item	Symbol	N-CHANNEL	Unit
Drain to Source Voltage ($V_{GS} = 0 V$)	V _{DSS}	20	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±12	V
Drain Current (DC) *1	I _{D(DC)}	±6.5	А
Drain Current (pulse) *2	I _{D(pulse)}	±60	А
Total Power Dissipation (2 unit) *1	P _{T1}	1.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Notes: *1. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt *2. PW \leq 10 μ s, Duty Cycle \leq 1%



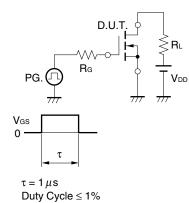
R07DS0185EJ0100 Rev.1.00 Dec 06, 2010

Item	Symbol	Min	Тур	Мах	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 20 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±10	μA	V _{GS} = ±12 V, V _{DS} = 0 V
Gate to Source Cut-off Voltage	V _{GS(off)}	0.5	1.0	1.5	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance *1	y _{fs}	2.5			S	V _{DS} = 10 V, I _D = 3.0 A
Drain to Source On-state	R _{DS(on)1}	11	14.5	17.5	mΩ	V_{GS} = 4.5 V, I_D = 3.0 A
Resistance *1	R _{DS(on)2}	11.5	15	18.5	mΩ	V_{GS} = 4.0 V, I_D = 3.0 A
	R _{DS(on)3}	12	16.5	22	mΩ	V _{GS} = 3.1 V, I _D = 3.0 A
	R _{DS(on)4}	15.3	19	27.5	mΩ	V _{GS} = 2.5 V, I _D = 3.0 A
Input Capacitance	C _{iss}		810		pF	V _{DS} = 10 V,
Output Capacitance	Coss		110		pF	V _{GS} = 0 V,
Reverse Transfer Capacitance	C _{rss}		85		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		3		μs	V _{DD} = 10 V, I _D = 3.0 A,
Rise Time	t _r		6		μs	V _{GS} = 4 V,
Turn-off Delay Time	t _{d(off)}		15		μs	R _G = 6 Ω
Fall Time	t _f		11		μs	
Total Gate Charge	Q _G		8		nC	V _{DD} = 16 V,
Gate to Source Charge	Q _{GS}		1.5		nC	V _{GS} = 4 V,
Gate to Drain Charge	Q _{GD}		3		nC	I _D = 6.5 A
Body Diode Forward Voltage *1	V _{F(S-D)}		0.83		V	I _F = 6.5 A, V _{GS} = 0 V

Electrical Characteristics ($T_A = 25^{\circ}C$)

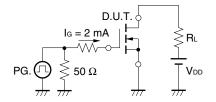
Note: *1. Pulsed

TEST CIRCUIT 1 SWITCHING TIME



Vgs 90% VGS Wave Form 0 10% Vgs VDS 90% 90% Vds 10% VDS Wave Form 10% 0 td(on) tr td(off) tf toff ton

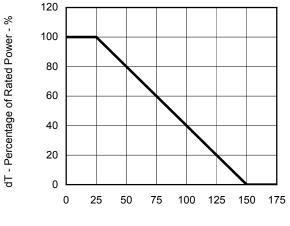
TEST CIRCUIT 2 GATE CHARGE





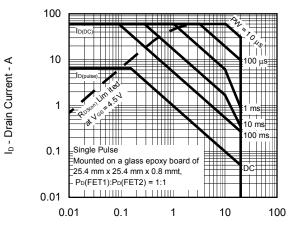
Typical Characteristics ($T_A = 25^{\circ}C$)

DERATING FACTOR OF FORWARD BIAS SAFE **OPERATING AREA**

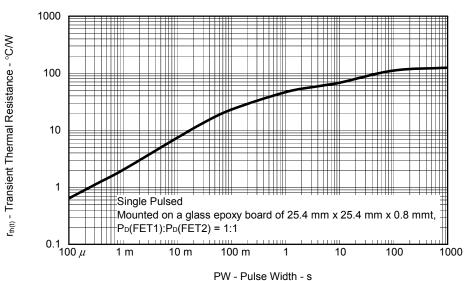


T_A - Ambient Temperature - °C

FORWARD BIAS SAFE OPERATING AREA



V_{DS} - Drain to Source Voltage - V

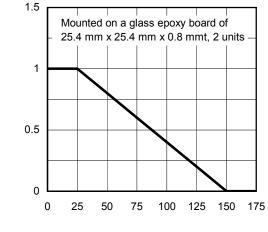


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

 $P_{\rm T}$ - Total Power Dissipation - W

AMBIENT TEMPERATURE

TOTAL POWER DISSIPATION vs.



T_A - Ambient Temperature - °C



I_D - Drain Current - A

V_{GS(off)} - Gate to Source Cut-off Voltage - V

1.5

1

0.5

0 ∟ -75

-25

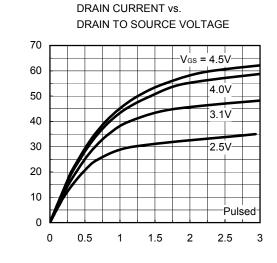
25

T_{ch} - Channel Temperature - °C

75

125

175



 $V_{\mbox{\scriptsize DS}}$ - Drain to Source Voltage - V

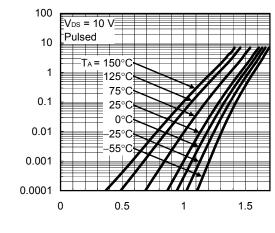
GATE TO SOURCE CUT-OFF VOLTAGE vs.

Vsp = 10 V

l_D = 1 mA

CHANNEL TEMPERATURE

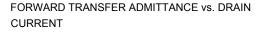
FORWARD TRANSFER CHARACTERISTICS

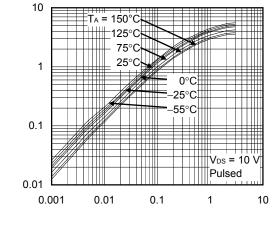


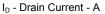
I_D - Drain Current - A

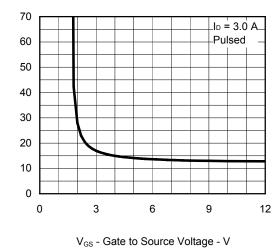
y_{fs} | - Forward Transfer Admittance - S

V_{GS} - Gate to Source Voltage - V



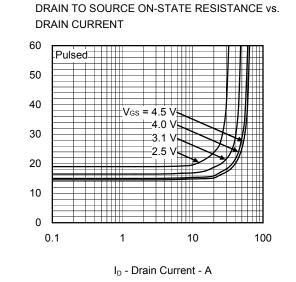






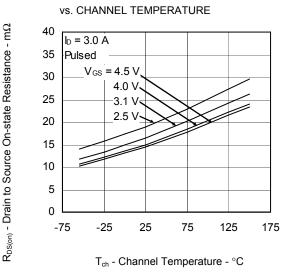
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

 $R_{DS(on)}$ - Drain to Source On-state Resistance - $m\Omega$



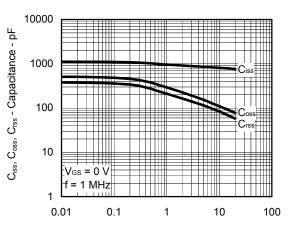


 $R_{DS(on)}$ - Drain to Source On-state Resistance - $m\Omega$



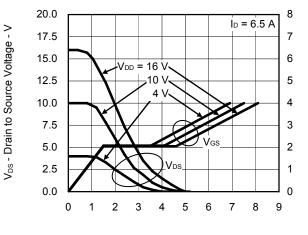
DRAIN TO SOURCE ON-STATE RESISTANCE

CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



V_{DS} - Drain to Source Voltage - V

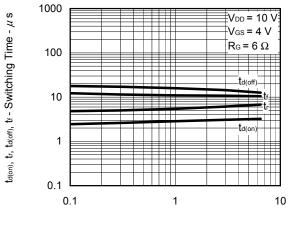
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



Q_G - Gate Charge - nC

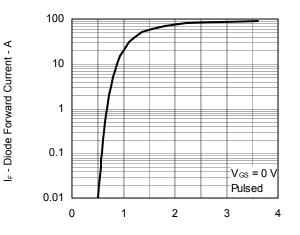
V_{GS} - Gate to Source Voltage - V





I_D - Drain Current - A

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



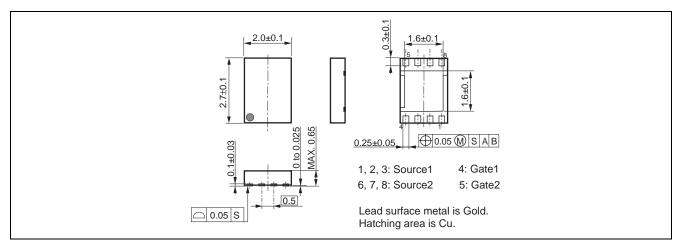
V_{F(S-D)} - Source to Drain Voltage - V

R07DS0185EJ0100 Rev.1.00 Dec 06, 2010

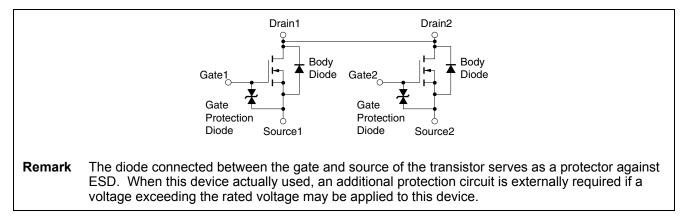


Package Drawings (Unit: mm)

8-pin HUSON (2720)



Equivalent Circuit





<Notes for using this device safely>

When you use this device, in order to prevent a customer's hazard and damage, use it with understanding the following contents. If used exceeding recommended conditions, there is a possibility of causing failure of the device and characteristic degradation.

- 1. When you mount the device on a substrate, carry out within our recommended soldering conditions of infrared reflow. If mounted exceeding the conditions, the characteristic of a device may be degraded and it may result in failure.
- 2. When you wash the device mounted the substrate, carry out within our recommended conditions. If washed exceeding the conditions, the characteristic of a device may be degraded and it may result in failure.
- 3. When you use ultrasonic wave to substrate after the device mounting, prevent from touching a resonance generator directly. If it touches, the characteristic of a device may be degraded and it may result in failure.
- 4. Please refer to **Figure 1** as an example of the land pattern. Optimize the land pattern in consideration of density, appearance of solder fillets, common difference, etc in an actual design.

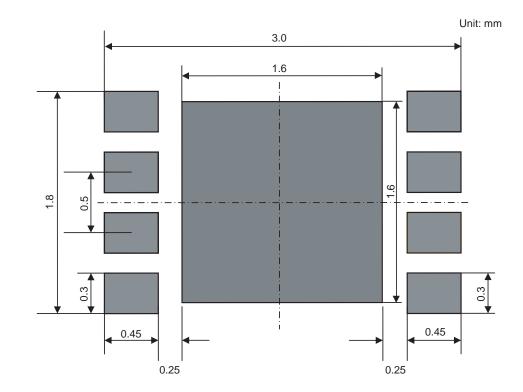


Figure 1. Example of the land pattern



Revision History	
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μ PA2460T1Q Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Dec 06, 2010	-	First Edition Issued	

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